

(43) International Publication Date
24 November 2011 (24.11.2011)(10) International Publication Number
WO 2011/146015 A1

(51) International Patent Classification:

H01L 33/00 (2010.01) *H01L 29/861* (2006.01)
H01L 21/328 (2006.01)

(21) International Application Number:

PCT/SG2010/000189

(22) International Filing Date:

18 May 2010 (18.05.2010)

(25) Filing Language:

English

(26) Publication Language:

English

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK,

[Continued on next page]

(54) Title: METHOD OF FORMING A LIGHT EMITTING DIODE STRUCTURE AND A LIGHT EMITTING DIODE STRUCTURE

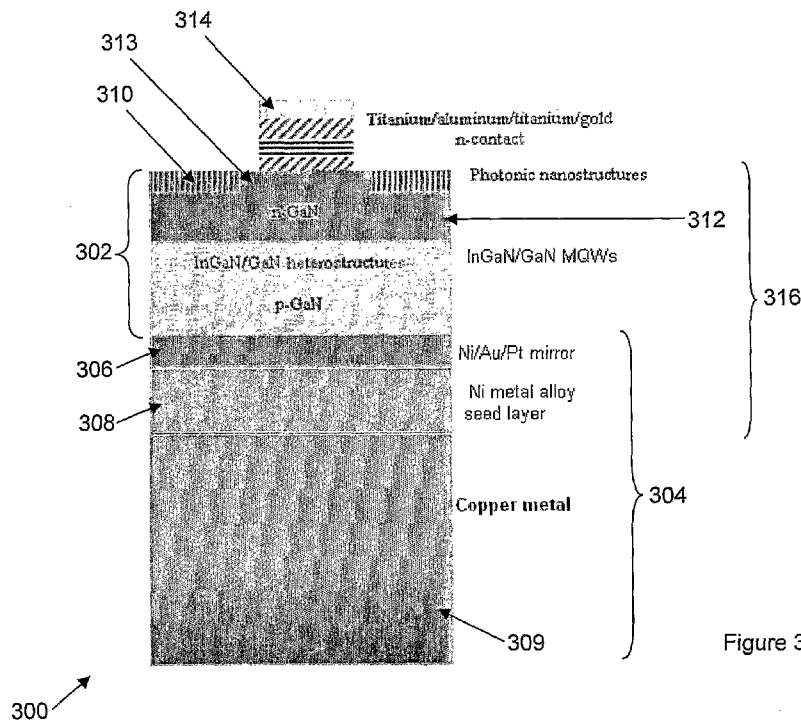


Figure 3

(57) Abstract: A method of forming a vertical III-nitride based light emitting diode structure and a vertical III-nitride based light emitting diode structure can be provided. The method comprises forming a III-nitride based light emitting structure on a silicon-on-insulator (SOI) substrate; forming a metal-based electrode structure on the III-nitride based light emitting structure; and removing the SOI substrate by a layer transfer process such that the metal-based electrode structure functions as a metal-based substrate of the light emitting structure.



EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, **Published:**

LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK,

SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, — *with international search report (Art. 21(3))*

GW, ML, MR, NE, SN, TD, TG).